



REF.	Min.	Max.	REF.	Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	500	V
Collector to Emitter Voltage	VCEO	400	V
Emitter to Base Voltage	VEBO	6.0	V
Collector Current	IC	300	mA
Total Power Dissipation	PD	1.2	W

**Characteristics at Ta = 25°C**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	500	-	-	V	IC=100uA
BVCEO	400	-	-	V	IC=1mA
BVEBO	6	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=400V
ICES	-	-	500	nA	VCB=400V
IEBO	-	-	100	nA	VEB=4V
VCE(sat)1	-	-	375	mV	IC=20mA, IB=2mA
VCE(sat)2	-	-	750	mV	IC=50mA, IB=5 mA
VBE(sat)	-	-	750	mV	IC=10mA, IB=1mA
hFE1	40	-	-		VCE=10V, IC=1mA
hFE2	50	-	300		VCE=10V, IC=10mA
hFE3	45	-	-		VCE=10V, IC=50mA
hFE4	40	-	-		VCE=10V, IC=100mA
Cob	-	4	6	pF	VCE=20V, f=1MHz

